In the Specification:

Please amend paragraph [0008] on page 4 and continuing on page 5 as follows:

[0008] In accordance with an embodiment of the present invention, a method of cleaning a semiconductor device is provided. The method comprises first applying a cleaning solution to a surface in the semiconductor device. An additive is then introduced into the cleaning solution. An emulsion is formed with the cleaning solution and the additive. Sonic waves are applied to the emulsion to induce cavitation, whereby bubbles are formed on the surface of the semiconductor device to facilitate removing particles from the surface. Preferably, the additive is an organic liquid. More preferably, the organic liquid is a straight-chained alcohol, a side-chained alcohol, a straight-chained alkane or a side-chained alkane. In one example, the organic liquid is immiscible or partly miscible and is capable of forming a hydrophobic phase (the cleaning solution may be viewed as the primary phase and the added material may be viewed as a second phase) in the cleaning solution.